

SD101AWS...SD101CWS Surface Mount Schottky Barrier Diodes

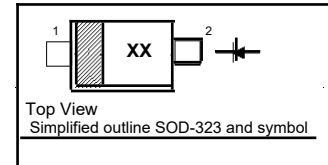
Features

- Low forward voltage
- Low reverse capacitance

INFORMATION

Type No.	Marking
SD101AW	S1
SD101BW	S2
SD101CW	S3

PIN	DESCRIPTION
1	Cathode
2	Anode



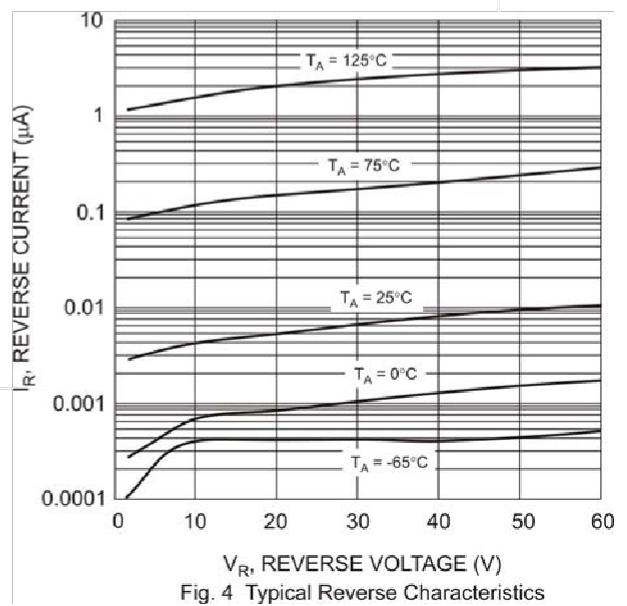
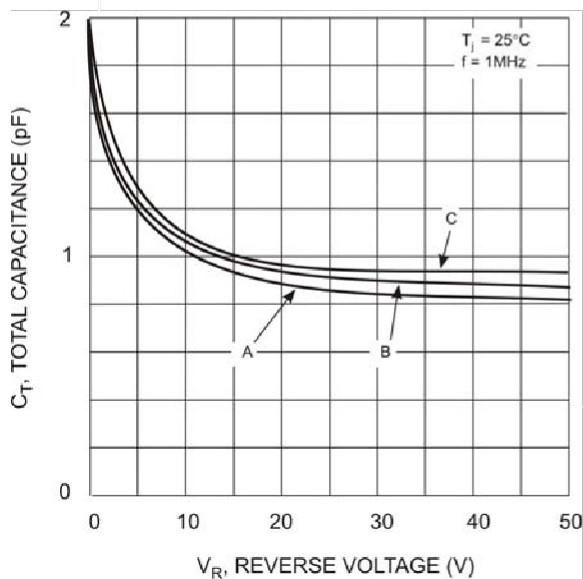
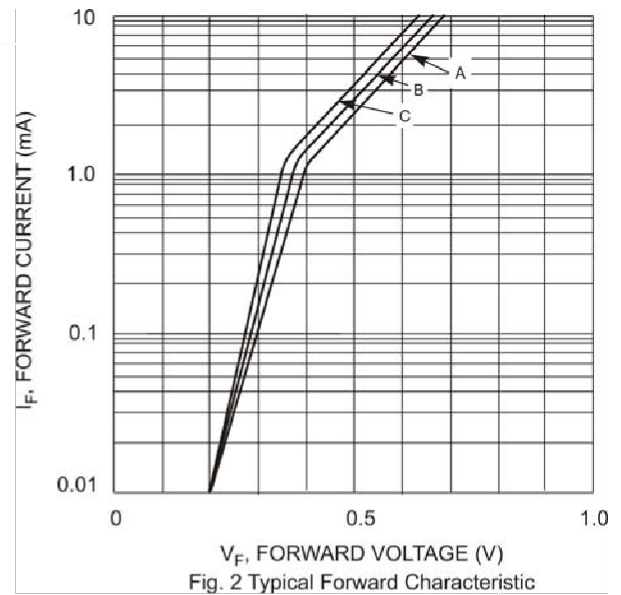
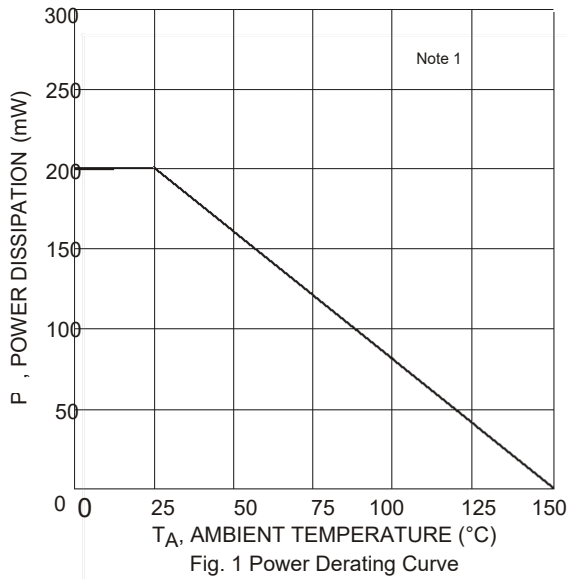
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60 50 40	V
Reverse Voltage	V_R	60 50 40	V
Forward Continuous Current	I_{FM}	15	mA
Power Dissipation	P_d	200	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Non-Repetitive Peak Forward Surge Current	I_{FSM}	50 2	mA A
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10 \mu\text{A}$	$V_{(BR)R}$	60 50 40	- - -	V
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 15 \text{ mA}$	V_F	- - - - -	0.41 0.4 0.39 1 0.95 0.9	V
Reverse Current at $V_R = 50 \text{ V}$ at $V_R = 40 \text{ V}$ at $V_R = 30 \text{ V}$	I_R	- - -	200 200 200	nA
Total Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	- - -	2 2.1 2.2	pF
Reverse Recovery Time at $I_F = I_R = 5 \text{ mA}, I_{TR} = 0.1X I_R, R_L = 100 \Omega$	t_{rr}	-	1	ns

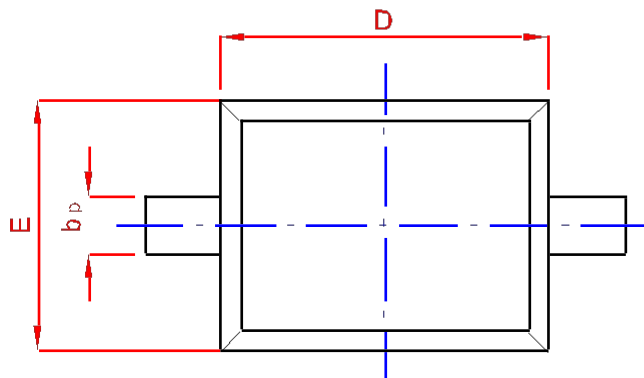
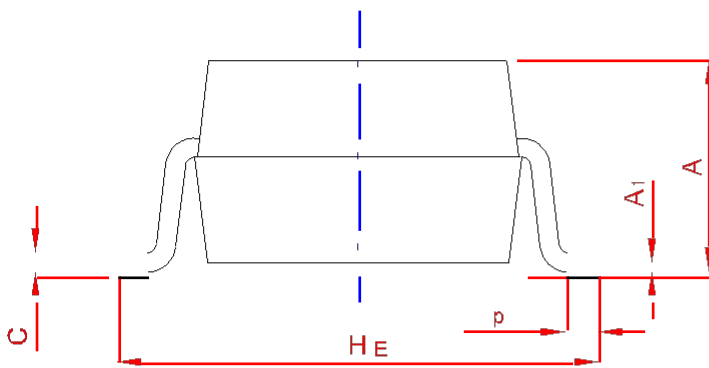
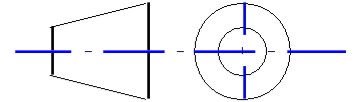
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20